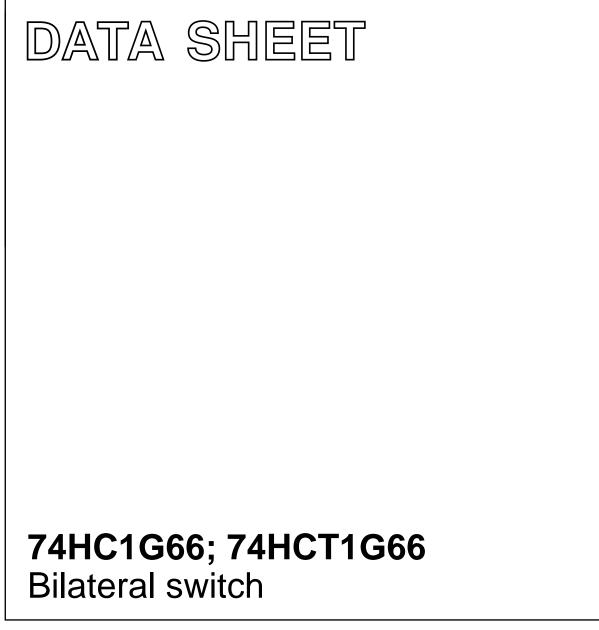
INTEGRATED CIRCUITS



Product specification Supersedes data of 2001 Mar 02 2002 May 15



Semiconductors

Philips

74HC1G66; 74HCT1G66

FEATURES

- Wide operating voltage range from 2.0 to 9.0 ${\rm V}$
- Very low ON-resistance:
 - 45 Ω (typical) at V_{CC} = 4.5 V
 - 30 Ω (typical) at V_{CC} = 6.0 V
 - 25 Ω (typical) at V_{CC} = 9.0 V.
- High noise immunity
- · Low power dissipation
- Very small 5 pins package
- Output capability: non standard.

QUICK REFERENCE DATA

GND = 0 V; $T_{amb} = 25 \text{ °C}$; $t_r = t_f = 6.0 \text{ ns}$.

DESCRIPTION

The 74HC1G/HCT1G66 is a high-speed Si-gate CMOS device.

The 74HC1G/HCT1G66 provides an analog switch. The switch has two input/output pins (Y and Z) and an active HIGH enable input pin (E). When pin E is LOW, the analog switch is turned off.

The non standard output currents are equal compared to the 74HC/HCT4066.

SYMBOL	PARAMETER	CONDITIONS	TYP	UNIT	
STIVIDUL		CONDITIONS	HC1G	HCT1G	UNIT
t _{PZH} /t _{PZL}	turn-on time E to V _{os}	$C_L = 15 \text{ pF}; R_L = 1 \text{ k}\Omega; V_{CC} = 5 \text{ V}$	11	12	ns
t _{PHZ} /t _{PLZ}	turn-off time E to V _{os}	$C_L = 15 \text{ pF}; R_L = 1 \text{ k}\Omega; V_{CC} = 5 \text{ V}$	11	12	ns
CI	input capacitance		1.5	1.5	pF
C _{PD}	power dissipation capacitance	notes 1 and 2	9	9	pF
C _S	maximum switch capacitance		8	8	pF

Notes

1. C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum ((C_L + C_S) \times V_{CC}^2 \times f_o)$ where:

 $f_i = input frequency in MHz;$

f_o = output frequency in MHz;

- C_L = output load capacitance in pF;
- C_S = maximum switch capacitance in pF;

V_{CC} = supply voltage in Volts;

 Σ ((C_L +C_S)× V_{CC}² × f_o) = sum of outputs.

2. For HC1G the condition is V_I = GND to V_{CC}. For HC11G the condition is V_I = GND to V_{CC} – 1.5 V.

FUNCTION TABLE

See note 1.

INPUT E	SWITCH
L	OFF
Н	ON

Note

H = HIGH voltage level;
L = LOW voltage level.

74HC1G66; 74HCT1G66

ORDERING INFORMATION

OUTSIDE NORTH	PACKAGE										
AMERICA	TEMPERATURE RANGE	PINS	PACKAGE	MATERIAL	CODE	MARKING					
74HC1G66GW	–40 to +125 °C	5	SC-88A	plastic	SOT353	HL					
74HCT1G66GW	–40 to +125 °C	5	SC-88A	plastic	SOT353	TL					
74HC1G66GV	–40 to +125 °C	5	SC-74A	plastic	SOT753	H66					
74HCT1G66GV	–40 to +125 °C	5	SC-74A	plastic	SOT753	T66					

PINNING

PIN	SYMBOL	DESCRIPTION			
1	Y	independent input/output Y			
2	Z independent input/output Z				
3	GND	ground (0 V)			
4	E	enable input E (active HIGH)			
5	V _{CC}	supply voltage			

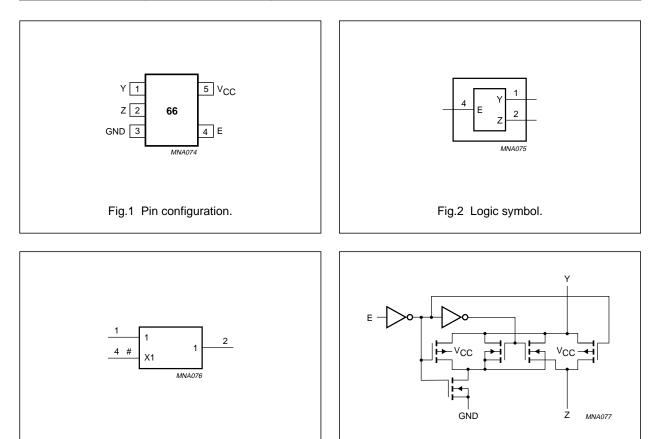


Fig.4 Logic diagram.

2002 May 15

Fig.3 IEC logic symbol.

74HC1G66; 74HCT1G66

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	CONDITIONS	7	4HC1G6	6	74HCT1G66			
STNIBUL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	UNIT
V _{CC}	supply voltage		2.0	5.0	10.0	4.5	5.0	5.5	V
VI	input voltage		GND	-	V _{CC}	GND	-	V _{CC}	V
Vs	switch voltage		GND	-	V _{CC}	GND	-	V _{CC}	V
T _{amb}	operating ambient temperature	see DC and AC characteristics per device	-40	-	+125	-40	-	+125	°C
t _r , t _f	input rise and fall times	V _{CC} = 2.0 V	-	-	1000	-	-	-	ns
		$V_{CC} = 4.5 V$	-	6.0	500	-	6.0	500	ns
		V _{CC} = 6.0 V	-	-	400	-	-	-	ns
		V _{CC} = 10.0 V	-	-	250	-	-	-	ns

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134); voltages are referenced to GND (ground = 0 V); see note 1.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CC}	supply voltage		-0.5	+11.0	V
I _{IK}	input diode current	$V_{I} < -0.5$ V or $V_{I} > V_{CC}$ + 0.5 V	-	±20	mA
I _{SK}	switch diode current	V_{S} < - 0.5 V or V_{S} > V_{CC} + 0.5 V	-	±20	mA
I _S	switch source or sink current	$-0.5 \text{ V} < \text{V}_{\text{S}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±25	mA
I _{CC}	V _{CC} or GND current		-	±50	mA
T _{stg}	storage temperature		-65	+150	°C
P _D	power dissipation per package	for temperature range from –40 to + 125 °C; note 2	-	200	mW
Ps	power dissipation per switch		-	100	mW

Notes

- To avoid drawing V_{CC} current out of pin Z, when switch current flows in pin Y, the voltage drop across the bidirectional switch must not exceed 0.4 V. If the switch current flows into pin Z, no V_{CC} current will flow out of terminal Y. In this case there is no limit for the voltage drop across the switch, but the voltage at pins Y and Z may not exceed V_{CC} or GND.
- 2. Above 55 $^\circ\text{C}$ the value of P_D derates linearly with 2.5 mW/K.

74HC1G66; 74HCT1G66

DC CHARACTERISTICS

Family 74HC1G66

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

	PARAMETER	TEST CONDITIO	ONS	T _{amb} (°C)					
SYMBOL		OTHER		−40 to +85			-40 t	o +125	UNIT
		OTHER	V _{CC} (V)	MIN.	TYP. ⁽¹⁾	MAX.	MIN.	MAX.	
V _{IH}	HIGH-level input		2.0	1.5	1.2	-	1.5	-	V
	voltage		4.5	3.15	2.4	-	3.15	-	V
			6.0	4.2	3.2	-	4.2	-	V
			9.0	6.3	4.7	-	6.3	-	V
VIL	LOW-level input		2.0	-	0.8	0.5	-	0.5	V
	voltage		4.5	-	2.1	1.35	-	1.35	V
			6.0	-	2.8	1.8	-	1.8	V
			9.0	-	4.3	2.7	-	2.7	V
ILI	input leakage	$V_I = V_{CC}$ or GND	6.0	-	0.1	1.0	-	1.0	μΑ
	current		10.0	-	0.2	2.0	-	2.0	μΑ
I _S	analog switch current, OFF-state		10.0	_	0.1	1.0	-	1.0	μΑ
	analog switch current, ON-state		10.0	_	0.1	1.0	-	1.0	μΑ
I _{CC}	quiescent supply	$V_I = V_{CC}$ or GND;	6.0	-	1.0	10	-	20	μA
	current	$V_{is} = GND \text{ or } V_{CC};$ $V_{os} = V_{CC} \text{ or } GND$	10.0	-	2.0	20	-	40	μΑ

Note

1. All typical values are measured at T_{amb} = 25 °C.

74HC1G66; 74HCT1G66

Family 74HCT1G66

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

		TEST CONDIT	IONS						
SYMBOL	PARAMETER		N 00	−40 to +85			-40 to +125		UNIT
		OTHER	V _{CC} (V)	MIN.	TYP. ⁽¹⁾	MAX.	MIN.	MAX.	
V _{IH}	HIGH-level input voltage		4.5 to 5.5	2.0	1.6	-	2.0	-	V
V _{IL}	LOW-level input voltage		4.5 to 5.5	0.1	1.2	0.8	-	0.8	V
ILI	input leakage current	$V_{I} = V_{CC} \text{ or } GND$	5.5	-	0.1	1.0	-	1.0	μA
I _S	analog switch current, OFF-state		5.5	-	0.1	1.0	-	1.0	μA
	analog switch current, ON-state		5.5	-	0.1	1.0	-	1.0	μA
I _{CC}	quiescent supply current		4.5 to 5.5	-	1	10	-	20	μA
ΔI _{CC}	additional supply current per input	$V_{I} = V_{CC} - 2.1 \text{ V}$	4.5 to 5.5	-	-	500	-	850	μA

Note

1. All typical values are measured at T_{amb} = 25 $^\circ C.$

74HC1G66; 74HCT1G66

Family 74HC1G66 and 74HCT1G66

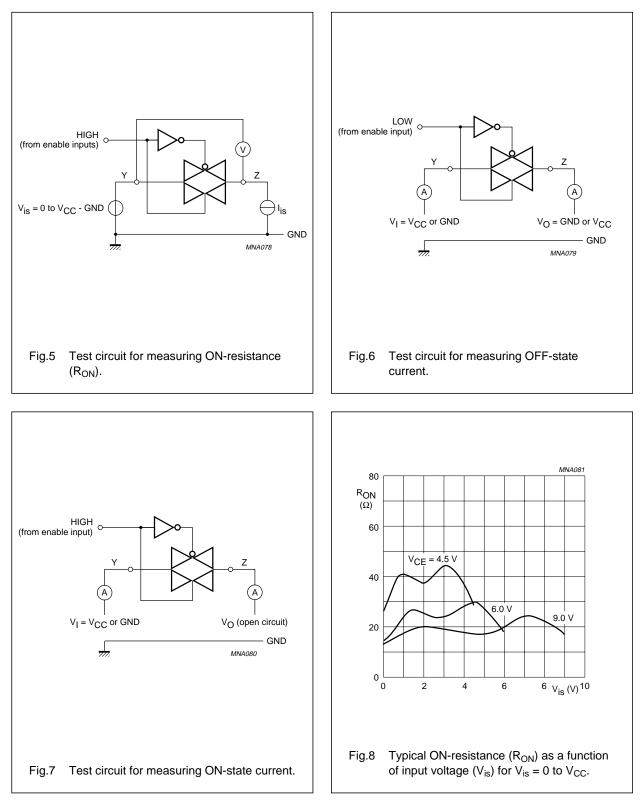
For 74HC1G66: V_{CC} = 2.0, 4.5, 6.0 or 9.0 V; note 1. For 74HCT1G66: V_{CC} = 4.5 V.

		TEST CONDIT	IONS			T,	amb (°C))		
SYMBOL	PARAMETER	OTHER	Vcc	Is	−40 to +85			-40 to +125		UNIT
		UTHER	(V)	(μΑ)	MIN.	TYP. ⁽²⁾	MAX.	MIN.	MAX.	
R _{ON}	ON-resistance	$V_{is} = V_{CC}$ to GND;	2.0	100	-	-	-	-	-	Ω
	(peak)	$V_{I} = V_{IH} \text{ or } V_{IL};$	4.5	1000	-	42	118	-	142	Ω
			6.0	1000	-	31	105	-	126	Ω
			9.0	1000	-	23	88	-	105	Ω
	ON-resistance		2.0	100	-	75	-	-	-	Ω
	(rail)	$V_I = V_{IH} \text{ or } V_{IL};$	4.5	1000	-	29	95	-	115	Ω
		see Fig.5	6.0	1000	-	23	82	-	100	Ω
			9.0	1000	-	18	70	-	80	Ω
		V _{is} = V _{CC} ;	2.0	100	-	75	-	-	-	Ω
	$V_{I} = V_{IH} \text{ or } V_{IL};$	=	4.5	1000	-	35	106	-	128	Ω
		see Fig.5	6.0	1000	-	27	94	-	113	Ω
			9.0	1000	-	21	78	-	95	Ω

Notes

- 1. At supply voltages approaching 2 V, the analog switch ON-resistance becomes extremely non-linear. Therefore it is recommended that these devices be used to transmit digital signals only, when using this supply voltage.
- 2. All typical values are measured at T_{amb} = 25 °C.

74HC1G66; 74HCT1G66



74HC1G66; 74HCT1G66

AC CHARACTERISTICS

Type 74HC1G66

GND = 0 V; $t_r = t_f = 6 ns$.

		TEST CONDITIO	NS						
SYMBOL	PARAMETER	WAVEFORMS		−40 to +85			-40 to +125		UNIT
		WAVEFORWS	V _{CC} (V)	MIN.	TYP. ⁽¹⁾	MAX.	MIN.	MAX.	
t _{PHL} /t _{PLH}	propagation delay	$R_L = \infty; C_L = 50 \text{ pF};$	2.0	-	8	75	-	90	ns
	V _{is} to V _{os}	see Fig.12	4.5	-	3	15	-	18	ns
			6.0	-	2	13	-	15	ns
			9.0	-	1	10	-	12	ns
t _{PZH} /t _{PZL}	turn-on time	$R_L = 1 k\Omega; C_L = 50 pF;$	2.0	-	50	125	-	150	ns
	E to V _{os}	see Figs 13 and 14	4.5	-	16	25	-	30	ns
			6.0	-	13	21	-	26	ns
			9.0	-	9	16	-	20	ns
t _{PHZ} /t _{PLZ}	turn-off time	$R_L = 1 k\Omega; C_L = 50 pF:$	2.0	-	27	190	-	225	ns
	E to V _{os}	see Figs 13 and 14	4.5	-	16	38	-	45	ns
			6.0	-	14	33	-	38	ns
			9.0	-	12	16	-	20	ns

Note

1. All typical values are measured at $T_{amb} = 25 \ ^{\circ}C$.

Type 74HCT1G66

GND = 0 V; $t_r = t_f = 6 ns$; V_{is} is the input voltage at pins Y or Z, whichever is assigned as an input. V_{os} is the output voltage at pins Y or Z, whichever is assigned as an output.

		TEST CONDITIO	NS						
SYMBOL	PARAMETER		V _{CC} (V)	−40 to +85			-40 to +125		UNIT
		WAVEFORMS		MIN.	TYP. ⁽¹⁾	MAX.	MIN.	MAX.	
t _{PHL} /t _{PLH}	propagation delay V _{is} to V _{os}	$R_L = \infty$; $C_L = 50 \text{ pF}$; see Fig.12.	4.5	-	3	15	-	18	ns
t _{PZH} /t _{PZL}	turn-on time E to V _{os}	$R_L = 1 \text{ k}\Omega; C_L = 50 \text{ pF};$ see Figs 15 and 16.	4.5	-	15	30	-	36	ns
t _{PHZ} /t _{PLZ}	turn-off time E to V _{os}	$R_L = 1 \text{ k}\Omega; C_L = 50 \text{ pF};$ see Figs 15 and 16.	4.5	-	13	44	-	53	ns

Note

1. All typical values are measured at $T_{amb} = 25 \ ^{\circ}C$.

74HC1G66; 74HCT1G66

Type 74HC1G66 and 74HCT1G66

At recommended conditions and typical values. GND = 0 V; $t_r = t_f = 6.0 ns$. V_{is} is the input voltage at pins Y or Z, whichever is assigned as an input; V_{os} is the output voltage at pins Y or Z, whichever is assigned as an output.

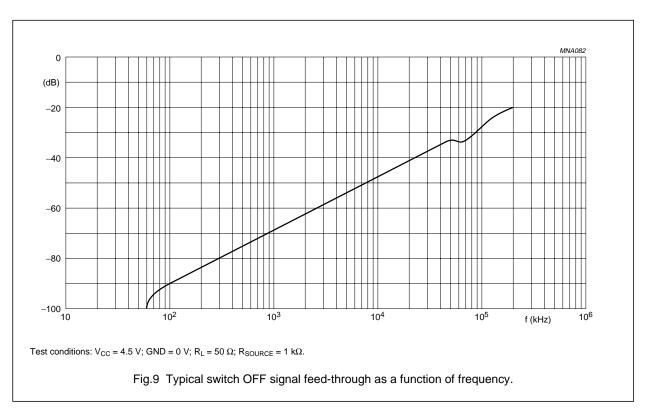
SYMBOL	PARAMETER	TEST CONDITIONS	V _{is(p-p)} (V)	V _{CC} (V)	TYP.	UNIT
	sine-wave distortion	$R_L = 10 \text{ k}\Omega; C_L = 50 \text{ pF}; \text{ see Fig.12}$	4.0	4.5	0.04	%
	f = 1 kHz		8.0	9.0	0.02	%
	sine-wave distortion	$R_L = 10 \text{ k}\Omega; C_L = 50 \text{ pF}; \text{ see Fig.12}$	4.0	4.5	0.12	%
	f = 10 kHz		8.0	9.0	0.06	%
	switch OFF signal	$R_L = 600 \Omega$; $C_L = 50 pF$; f = 1 MHz;	note 1	4.5	-50	dB
	feed-through	see Figs 9 and 13		9.0	-50	dB
f _{max}	minimum frequency	$R_L = 50 \Omega; C_L = 10 pF;$	note 2	4.5	180	MHz
	response (-3 dB)	see Figs 10 and 11		9.0	200	MHz
C _S	maximum switch capacitance				8	pF

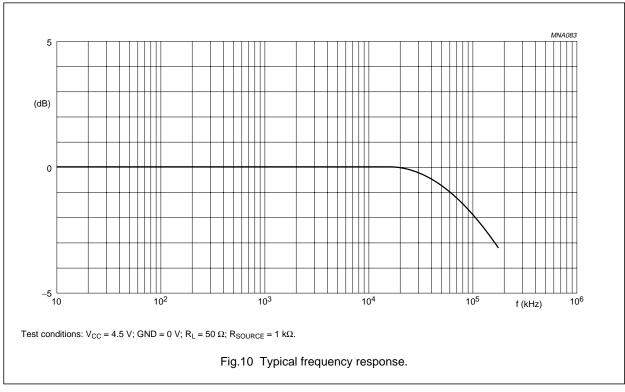
Notes

1. Adjust input voltage V_{is} is 0 dBm level (0 dBM = 1 mW into 600 Ω).

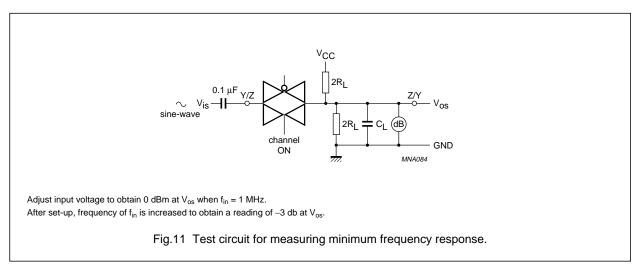
2. Adjust input voltage V_{is} is 0 dBm level at V_{os} for 1 MHz (0 dBM = 1 mW into 50 Ω).

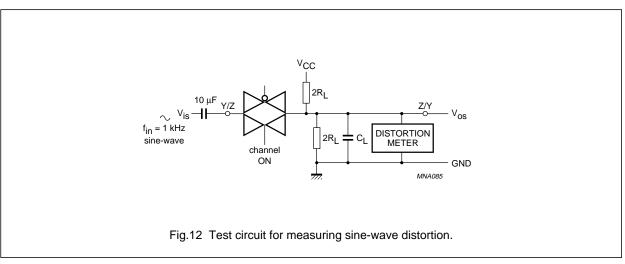
74HC1G66; 74HCT1G66

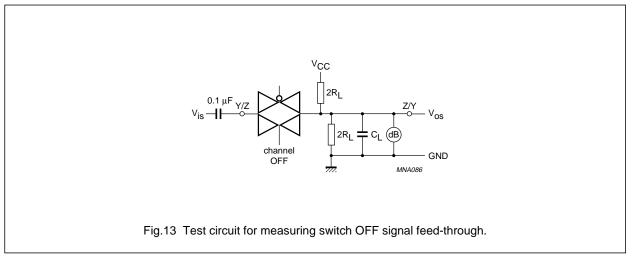




74HC1G66; 74HCT1G66

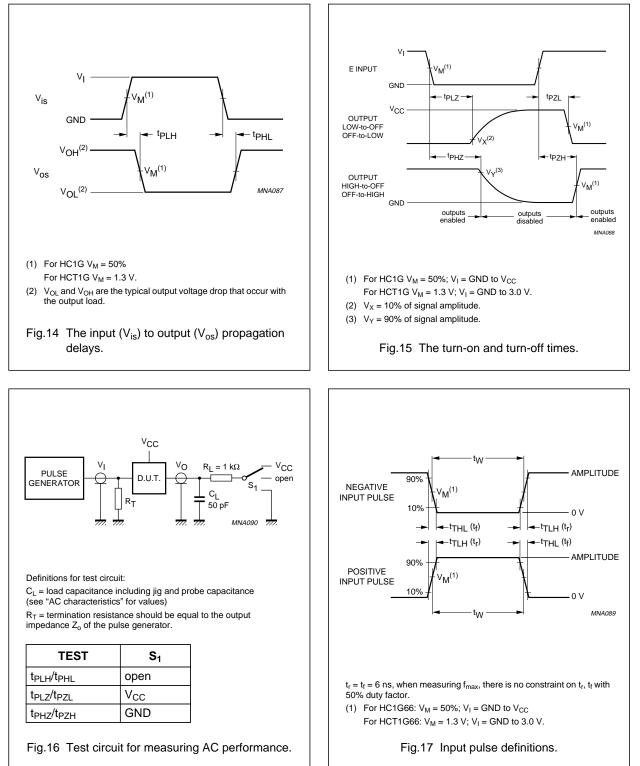






74HC1G66; 74HCT1G66

AC WAVEFORMS

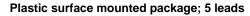


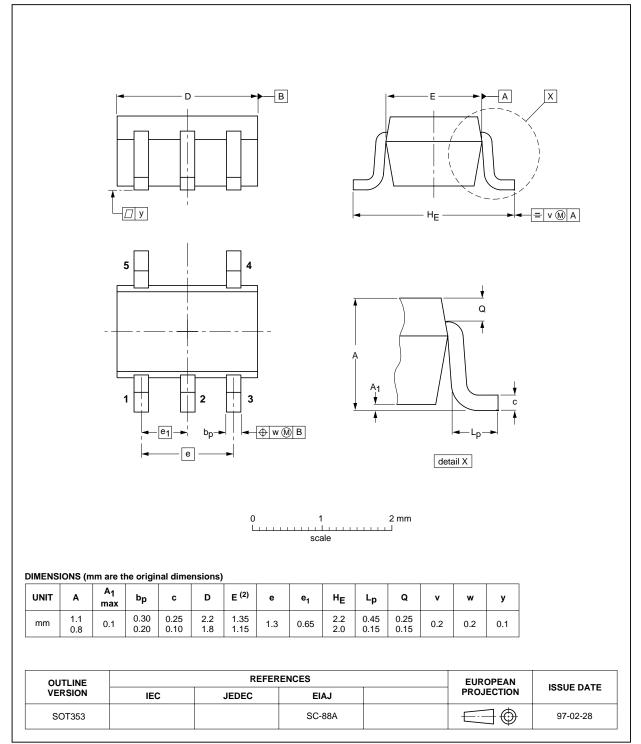
SOT353

Bilateral switch

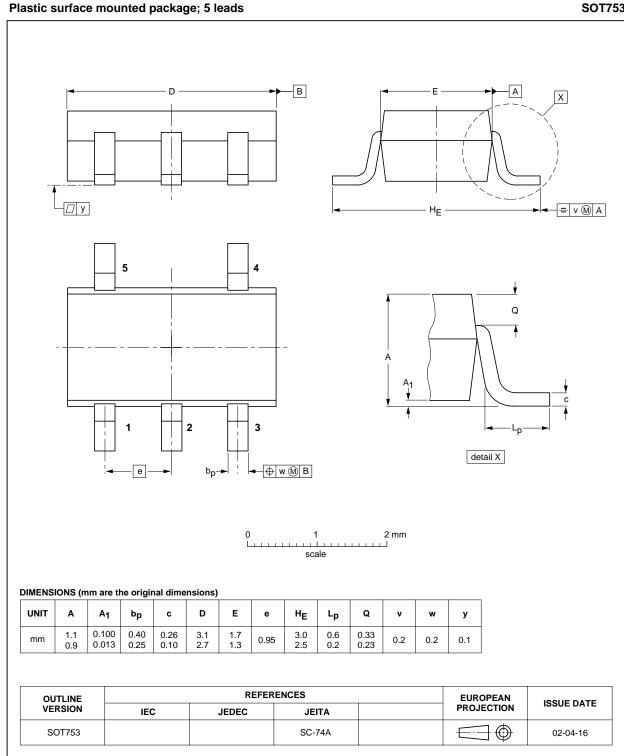
74HC1G66; 74HCT1G66

PACKAGE OUTLINES





74HC1G66; 74HCT1G66



SOT753

74HC1G66; 74HCT1G66

SOLDERING

Introduction to soldering surface mount packages

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our "*Data Handbook IC26; Integrated Circuit Packages*" (document order number 9398 652 90011).

There is no soldering method that is ideal for all surface mount IC packages. Wave soldering can still be used for certain surface mount ICs, but it is not suitable for fine pitch SMDs. In these situations reflow soldering is recommended.

Reflow soldering

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several methods exist for reflowing; for example, convection or convection/infrared heating in a conveyor type oven. Throughput times (preheating, soldering and cooling) vary between 100 and 200 seconds depending on heating method.

Typical reflow peak temperatures range from 215 to 250 °C. The top-surface temperature of the packages should preferable be kept below 220 °C for thick/large packages, and below 235 °C for small/thin packages.

Wave soldering

Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems.

To overcome these problems the double-wave soldering method was specifically developed.

If wave soldering is used the following conditions must be observed for optimal results:

- Use a double-wave soldering method comprising a turbulent wave with high upward pressure followed by a smooth laminar wave.
- For packages with leads on two sides and a pitch (e):
 - larger than or equal to 1.27 mm, the footprint longitudinal axis is **preferred** to be parallel to the transport direction of the printed-circuit board;
 - smaller than 1.27 mm, the footprint longitudinal axis must be parallel to the transport direction of the printed-circuit board.

The footprint must incorporate solder thieves at the downstream end.

 For packages with leads on four sides, the footprint must be placed at a 45° angle to the transport direction of the printed-circuit board. The footprint must incorporate solder thieves downstream and at the side corners.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Typical dwell time is 4 seconds at 250 °C. A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

Manual soldering

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24 V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to $300 \,^{\circ}$ C.

When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 $^{\circ}$ C.

74HC1G66; 74HCT1G66

Suitability of surface mount IC packages for wave and reflow soldering methods

	SOLDERING METHOD	
FACKAGE	WAVE	REFLOW ⁽²⁾
BGA, LBGA, LFBGA, SQFP, TFBGA, VFBGA	not suitable	suitable
HBCC, HBGA, HLQFP, HSQFP, HSOP, HTQFP, HTSSOP, HVQFN, HVSON, SMS	not suitable ⁽³⁾	suitable
PLCC ⁽⁴⁾ , SO, SOJ	suitable	suitable
LQFP, QFP, TQFP	not recommended ⁽⁴⁾⁽⁵⁾	suitable
SSOP, TSSOP, VSO	not recommended ⁽⁶⁾	suitable

Notes

- 1. For more detailed information on the BGA packages refer to the "(*LF*)BGA Application Note" (AN01026); order a copy from your Philips Semiconductors sales office.
- 2. All surface mount (SMD) packages are moisture sensitive. Depending upon the moisture content, the maximum temperature (with respect to time) and body size of the package, there is a risk that internal or external package cracks may occur due to vaporization of the moisture in them (the so called popcorn effect). For details, refer to the Drypack information in the "Data Handbook IC26; Integrated Circuit Packages; Section: Packing Methods".
- 3. These packages are not suitable for wave soldering. On versions with the heatsink on the bottom side, the solder cannot penetrate between the printed-circuit board and the heatsink. On versions with the heatsink on the top side, the solder might be deposited on the heatsink surface.
- 4. If wave soldering is considered, then the package must be placed at a 45° angle to the solder wave direction. The package footprint must incorporate solder thieves downstream and at the side corners.
- 5. Wave soldering is suitable for LQFP, TQFP and QFP packages with a pitch (e) larger than 0.8 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.65 mm.
- 6. Wave soldering is suitable for SSOP and TSSOP packages with a pitch (e) equal to or larger than 0.65 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.5 mm.

74HC1G66; 74HCT1G66

DATA SHEET STATUS

DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITIONS	
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.	
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.	
Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A.	

Notes

- 1. Please consult the most recently issued data sheet before initiating or completing a design.
- 2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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NOTES

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